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1/f Noise Characterization in CMOS Transistors in 0.13μm Technology

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Abstract

Low-frequency noise has been studied on a set of n- and p-channel CMOS transistors fabricated in a 0.13μm technology. Noise measurements have been performed on transistors with different gate lengths operating under wide bias conditions, ranging from weak to strong inversion. Noise origin has been identified for both type of devices, and the oxide trap density \( N_t \), the Hooge parameter \( \alpha_H \), and the Coulomb scattering parameter \( \alpha_s \) have been extracted. The experimental results are compared with simulations using the BSIM3v3 MOS model.

2. Noise Models

Two main theories are used to describe the origin of 1/f noise in MOS transistors.

McWhorter carrier number fluctuations (\( \Delta N \)) theory explains the noise origin by the fluctuations of the channel free carriers due to the random trapping and detrapping of charges in the oxide traps near the Si-SiO\(_2\) interface. Theoretical formulation for the drain current power spectral density \( S_{ID} \) based on the \( \Delta N \) theory proposed by Reimbold [7] and Van Der Ziel [8] for transistors working in weak inversion, is given by

\[
S_{ID} = \frac{q^4 N_t}{kT W L^2 \gamma C_{ox}^2 \eta^2} \frac{I^2_D}{f} \tag{1}
\]

where \( N_t \) is the trap density, \( \gamma \) (10\(^8\)/cm) is the tunnelling constant for the traps, and \( \eta \) is the weak inversion slope factor, given by \((C_{ox}+C_D+C_{it})/C_{ox}\), with \( C_{ox}, C_D \) and \( C_{it} \) being the oxide, depletion and interface trap capacitances per unit area, respectively (\( W, L, q, kT \) have their usual meaning). Experimental results in general show that the formalism (1) explains very well 1/f noise in weak inversion. In fact, the value of \( N_t \) can be extracted from noise measurements against drain current, if other parameters from (1) are known. Furthermore, this parameter is related to the BSIM noise parameter NOIA as \( N_t = NOIA/\gamma \).

For transistors working in strong inversion in the ohmic range, the \( \Delta N \)-based model of \( S_{ID} \) can be expressed by [9]

\[
S_{ID} = \frac{q^2 kT N_t \mu_{eff}^2}{\gamma} \frac{W}{L^3} \frac{V_{DS}^2}{f} \tag{2}
\]

with \( V_{DS} \) being drain-source voltage and \( \mu_{eff} \) effective mobility.

The second 1/f noise theory, Hooge mobility fluctuation (\( \Delta \mu \)) theory [3], explains the origin of 1/f noise by the fluctuations of bulk mobility with the empirical relation for homogeneous semiconductors, given by

\[
S_{ID} = \frac{\alpha_H I^2_D}{N f} \tag{3}
\]

where \( \alpha_H \) is Hooge parameter, constant for a given technology and \( N \) the total number of carriers under the gate. After estimation of \( N \), it can be shown [9] that for a MOS transistor working in the linear region the following applies

\[
S_{ID} = \alpha_H \mu_{eff}^2 W \frac{V_{GS} - V_{th}}{L^3} \frac{V_{DS}^2}{f} \tag{4}
\]
The measured 1/f noise in n-MOS transistors in strong inversion in the ohmic region usually shows constant $S_{ID}/f^{2}$ versus gate bias voltage, in agreement with (2), which can not be predicted by the $\Delta \mu$ model, because of the bias-independent $\alpha_f^2$; thus, the 1/f noise origin for n-devices is attributed to the number fluctuation theory. On the other hand, the observed dependence on the gate bias for the same region for p-channel transistors is following the $\Delta \mu$ theory, in line with equation (4), and can not be explained by $\Delta N$. However, quadratic variation of $S_{ID}$ versus drain current, following the $\Delta N$ model described by (1), is observed for both n- and p-transistors in weak inversion, and can not be explained by the Hooge model. This controversy, known from the experiments published in the literature, has been observed in our experiments as well, which will be presented in the next section.

Recent modelling efforts combine the two previously described approaches in the correlated number and mobility fluctuations $\Delta N-\Delta \mu$ model [4]-[5], in an attempt to come to a universal model valid for both n- and p-channel transistors in all operation regions. This model takes into account that the oxide/interface traps, apart from modulating the number of carriers, indirectly interact with the carrier mobility through Coulomb scattering. By this approach, the normalized drain current noise spectral density takes the form presented by Ghibaudo [5]

$$S_{ID} = \frac{1}{f} \left[ 1 + \alpha f \mu e f f C_{ox} \left( \frac{g_m}{\mu_{ID}} \right)^2 \right] S_{Vfb}$$

(5)

where $\alpha_f$ is scattering parameter and $S_{Vfb}$ is the flatband voltage spectral density given by

$$S_{Vfb} = \frac{q^2 k T N_t}{\gamma W L C_{ox}^2 f}$$

(6)

Since for weak inversion

$$\frac{g_m}{\mu_{ID}} \approx \frac{q}{k T} \frac{1}{\eta}$$

(7)

and by neglecting the scattering term in (5), it can be noticed that

$$S_{ID} = \frac{g_m}{\mu_{ID}} \frac{2}{S_{Vfb}}$$

(8)

equals equation (1). Similarly, by plugging in the formulas for $\mu_e f f$ and $\frac{g_m}{\mu_{ID}}$ in the linear region in (5), it can be shown that the input referred noise voltage density takes the form

$$S_{Vg} = \left[ 1 + \alpha f \mu_0 C_{ox}(V_{GS} - V_{th}) \right] S_{Vfb}$$

(9)

where $\mu_0$ is the low-field mobility and $V_{GS}$ the gate-source voltage.

The $\Delta N-\Delta \mu$ model described shows a satisfactory fitting to the experimental data for both p- and n-channel devices. However, critical discussions on its exactness exist [10]. A form of the unified model noise expression (5)-(9) is implemented in the BSIM3v3 circuit simulator model [6].

### 3. Experimental Study

#### 3.1. Measurement Set-Up

The devices studied are fabricated in a 0.13 $\mu$m CMOS technology with oxide thickness 2.4 nm, n+/p+ poly gate, shallow trench isolation and Co-silicided drain, source and gate. All the transistors tested have width $W=10 \mu$m and different lengths. Transistors of the same type have common gate, source and bulk connections, and separate drains. Prior to noise measurements, DC characteristics $I_D(V_{GS})$ and $g_m(V_{GS})$ have been measured. From the DC characteristics $I_{DS}=50mV$ using the function $\frac{I_{DS}}{V_{GS}}$ as described in [11], the conduction parameters $\mu_0$, $V_{th}$, $\Delta L$ and $S=(\frac{dl_{eqV_{GS}}}{dV_{GS}})_{-1} = 2.3 \frac{k T n}{q}$, given in Table 1, have been extracted for both p- and n-transistors. The drain current noise of the tested devices has been amplified by a low-noise amplifier AD7071N connected in a transconductance configuration, and measured for different transistor bias voltages. The amplifier has been biased using batteries, while the variable voltage supplies to the DUT have been generated from a PC using the N162899 high precision data acquisition card. The same card has been used for measurements with the noise spectra obtained with help of NI software. Lorentzian-like spectra usually observed on the top of 1/f noise for small area or minimum size devices have not been taken into account. The same noise behavior has been observed on three measured samples.

#### 3.2. Results Discussion

The plots of the normalized drain current power spectral density $S_{ID}/I_{ID}^2$, and the corresponding $(g_m/I_{ID})^2$ ratio versus drain current are shown in Fig. 1 and Fig. 2 for n- and p-transistors respectively, working in the ohmic region. Analysis of these plots is considered a generic procedure to distinguish between the 1/f noise mechanisms. As explained by equations (5)-(8), if there is a good correlation of the normalized drain current noise with the corresponding transconductance to drain current ratio squared, the $\Delta N$ model dominates, which is clearly the case for our n-transistors. On the other hand, for p-transistors in Fig. 2, a departure from the $(g_m/I_{ID})^2$ characteristics in strong inversion can be explained by the influence of additional correlated mobility fluctuation. From the $S_{ID}/I_{ID}^2$ weak inversion plateau, using the equation (1) and the slope factor value from Table 1, the $N_f$ values are calculated. For both types of devices, the value of $N_f$ is about $3.5 \times 10^{-17} - 4.5 \times 10^{17}$ (eV$^{-1}$cm$^{-3}$). The value of $N_f$ for n-transistors in strong inversion matches the one for weak inversion.

The input-referred noise power spectral density is plotted in Fig. 3 as a function of the effective gate-source volt-

<table>
<thead>
<tr>
<th>$L$ $(\mu$m)</th>
<th>0.13</th>
<th>0.26</th>
<th>0.5</th>
<th>1</th>
<th>2</th>
</tr>
</thead>
<tbody>
<tr>
<td>$V_{thn}(V)$</td>
<td>0.41</td>
<td>0.395</td>
<td>0.372</td>
<td>0.360</td>
<td>0.336</td>
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<tr>
<td>$V_{thp}(V)$</td>
<td>0.365</td>
<td>0.364</td>
<td>0.353</td>
<td>0.349</td>
<td>0.346</td>
</tr>
<tr>
<td>$S_{n}(mV/dec)$</td>
<td>86.25</td>
<td>84.97</td>
<td>84.19</td>
<td>95.7</td>
<td>97.05</td>
</tr>
<tr>
<td>$S_{p}(mV/dec)$</td>
<td>96.32</td>
<td>87.62</td>
<td>91.66</td>
<td>92.6</td>
<td>94.5</td>
</tr>
<tr>
<td>$\Delta L_n$ $(\mu$m)</td>
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<td></td>
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<td>$\Delta L_p$ $(\mu$m)</td>
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<td></td>
<td>0.015</td>
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<tr>
<td>$\mu_{on}$ $(cm^2/Vs)$</td>
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<td></td>
<td></td>
<td>221</td>
<td></td>
</tr>
<tr>
<td>$\mu_{off}$ $(cm^2/Vs)$</td>
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<td></td>
<td></td>
<td>60</td>
<td></td>
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</tbody>
</table>

Table 1: Extracted Transistor Conduction Parameters ($W=10\mu$m) for n- and p-MOS.
Figure 1: Normalized drain current noise $S_{ID}/I_D^2$ and $(g_m/I_D)^2$ ratio off (-) versus drain current for $V_{DS}=50\text{mV}$ for NMOS with various transistor lengths. $L=0.26(\square)$, 0.5 ($\times$), 1 ($\bullet$) and 2 (+) $\mu$m.

Figure 2: Normalized drain current $S_{ID}/I_D^2$ noise and $(g_m/I_D)^2$ ratio (-) versus drain current for $V_{DS}=50\text{mV}$ for various PMOS transistor lengths. $L=0.26(\square)$, 0.5 ($\times$) and 1 ($\bullet$) $\mu$m.

Figure 3: Input referred noise $S_{Vg}$ versus gate overdrive voltage for $V_{DS}=50\text{mV}$ for various NMOS transistor lengths. Simulation (-), $L=0.26(\square)$, 0.5 ($\times$), 1 ($\bullet$) and 2 (+) $\mu$m.

Figure 4: Input referred noise $S_{Vg}$ versus gate overdrive voltage for $V_{DS}=50\text{mV}$ for various PMOS transistor lengths. Simulation (-), $L=0.26(\square)$, 0.5 ($\times$) and 1 ($\bullet$) $\mu$m.

It can be seen in Fig. 3 that the model provides different value of the flatband voltage, compared to the measured one. The mean value of $\alpha_H$ for p-transistors with different dimensions is about $4.5 \cdot 10^{-4}$. This value is obtained from the measurement data by using a formula similar to (4) with $S_{ID}$ expressed as a function of $I_D$, $V_{GS}$ [9] that does not require the measurement of mobility attenuation factor $\theta$. The values of $\alpha_s$ for p-channel transistors, extracted using (9), have values $7.5 \cdot 10^3 - 9.5 \cdot 10^3$ (Vs/C). The values extracted are similar to the the values reported for the same technology node [13].

$S_{ID}$ versus drain current for $V_{DS}=0.45\text{V}$ for various dimensions of p- and n-transistors is shown in Fig. 5 and 6, along with the simulated data. As expected, the drain current spectral density shows a quadratic dependence on the drain current in weak inversion for $V_{DS}=450\text{mV}$ as well as for $V_{DS}=50\text{mV}$. As for the transistors working in linear region, measurements for p-channel transistors match very well simulations, while for n-transistors discrepancies are observed. The slope of the curve of $S_{ID}$ versus...
drain current is the same for measured and simulated data in Fig. 5 while the measured values are somehow greater than simulated.

![Figure 5](image)

Figure 5: Drain noise spectral density $S_{f, d}$ versus drain current for $V_{DS}=450\text{mV}$ for various NMOS transistor lengths. Simulation (-), $L=0.26(\square)$, 0.5 ($\times$), 1 ($\bullet$) and 2 (+) $\mu$m.

![Figure 6](image)

Figure 6: Drain noise spectral density $S_{f, d}$ versus drain current for $V_{DS}=450\text{mV}$ for various PMOS transistor lengths. Simulation (-), $L=0.26(\square)$, 0.5 ($\times$) and 1 ($\bullet$) $\mu$m.

4. Conclusion

In this work, low frequency noise has been investigated on MOS transistors from 0.13 $\mu$m technology. It has been observed that the noise in n-transistors originates from the number fluctuation theory, while the noise in p-MOS is due to the number fluctuations with correlated mobility fluctuations. Values of the physical parameters extracted match well the values for similar technologies. The simulation result show very good match with the measured data for p-transistors, while some discrepancies for n-transistors are observed.

5. Acknowledgments

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6. References

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